Shigeki Sakai

List of Publications by Year
in descending order

144 papers	3,022 citations	236925 25 h-index	189892 50 g-index
146 all docs	146 docs citations	146 times ranked	1489 citing authors

#	Article	IF	Citations
1	Area-Scalable 109-Cycle-High-Endurance FeFET of Strontium Bismuth Tantalate Using a Dummy-Gate Process. Nanomaterials, 2021, 11, 101.	4.1	11
2	A time-domain analog weighted-sum calculation circuit using ferroelectric-gate field-effect transistors for artificial intelligence processors. Japanese Journal of Applied Physics, 2020, 59, 040604.	1.5	3
3	Downsizing of High-Endurance and Long-Retention Pt/CaySr1â^'yBi2Ta2O9/(HfO2)x(Al2O3)1â^'x/Si FeFETs. Topics in Applied Physics, 2020, , 61-77.	0.8	0
4	Development of High-Endurance and Long-Retention FeFETs of Pt/CaySr1â^'yBi2Ta2O9/(HfO2)x(Al2O3)1â^'x/Si Gate Stacks. Topics in Applied Physics, 2020, , 23-60.	0.8	1
5	Novel Application of FeFETs to NAND Flash Memory Circuits. Topics in Applied Physics, 2020, , 319-341.	0.8	0
6	Investigation of Ferroelectric Grain Sizes and Orientations in Pt/CaxSr1â€“xBi2Ta2O9/Hfâ€“Alâ€“O/Si High Performance Ferroelectric-Gate Field-Effect-Transistors. Materials, 2019, 12, 399.	2.9	7
7	High-Endurance Ferroelectric NOR Flash Memory Using (Ca,Sr)Bi2Ta2O9 FeFETs. , 2018, , .		7
8	Method for disclosing invisible physical properties in metalâ^'ferroelectricâ^'insulatorâ^'semiconductor gate stacks. Journal Physics D: Applied Physics, 2017, 50, 165107.	2.8	7
9	3.3 V write-voltage Ir/Ca_{0.2}Sr_{0.8}Bi₂Ta₂O₉/HfO₂/Si ferroelectric-gate field-effect transistors with 10⁹endurance and good retention. Japanese Journal of Applied Physics, 2017, 56, 04CE04.	1.5	11
10	Dynamic Analog Characteristics of 10^9 Cycle-Endurance Low-Voltage Nonvolatile Ferroelectric-Gate Memory Transistors. , 2017, , .		3
11	Precise understanding of ferroelectric properties in metal/ferroelectric/insulator/semiconductor FETs with (Ca,Sr)Bi<inf>2</inf>Ta<inf>2</inf>O<inf>9</inf>. , 2017, , .		0
12	Compact model of ferroelectric-gate field-effect transistor for circuit simulation based on multidomain Landauâ€“Kalathnikov theory. Japanese Journal of Applied Physics, 2017, 56, 04CE07.	1.5	7
13	Ferroelectric-Gate Field Effect Transistor Memories. Topics in Applied Physics, 2016, , .	0.8	62
14	Novel Application of FeFETs to NAND Flash Memory Circuits. Topics in Applied Physics, 2016, , 271-293.	0.8	0
15	Novel process for widening memory window of sub-200 nm ferroelectric-gate field-effect transistor by ferroelectric coating the gate-stack sidewall. Semiconductor Science and Technology, 2015, 30, 015024.	2.0	8
16	100-nm-size ferroelectric-gate field-effect transistor with 10⁸-cycle endurance. Japanese Journal of Applied Physics, 2015, 54, 088004.	1.5	16
17	Electrical properties of Ca_xSr_{1â^'x}Bi₂Ta₂O₉ferroelectric-gate field-effect transistors. Semiconductor Science and Technology, 2013, 28, 085003.	2.0	14
18	FeFET Logic Circuits for Operating A 64 kb FeNAND Flash Memory Array. Integrated Ferroelectrics, 2012, 132, 114-121.	0.7	15

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19	64 kbit Ferroelectric-Gate-Transistor-Integrated NAND Flash Memory with 7.5 V Program and Long Data Retention. Japanese Journal of Applied Physics, 2012, 51, 04DD01.	1.5	12
20	Electrical properties of ferroelectric-gate FETs with SrBi2Ta2O9 formed using MOCVD technique. Applied Physics A: Materials Science and Processing, 2012, 108, 835-842.	2.3	17
21	Downsizing and memory array integration of Pt/SrBi2Ta2O9/Hf-Al-O/Si ferroelectric-gate field-effect transistors. , 2012, , .		7
22	64 kbit Ferroelectric-Gate-Transistor-Integrated NAND Flash Memory with 7.5 V Program and Long Data Retention. Japanese Journal of Applied Physics, 2012, 51, 04DD01.	1.5	34
23	Initialize and Weak-Program Erasing Scheme for High-Performance and High-Reliability Ferroelectric NAND Flash Solid-State Drive. IEICE Transactions on Electronics, 2012, E95.C, 609-616.	0.6	0
24	0.5V Bit-Line-Voltage Self-Boost-Programming in Ferroelectric-NAND Flash Memory. , 2011, , .		6
25	Downsizing of Ferroelectric-Gate Field-Effect-Transistors for Ferroelectric-NAND Flash Memory Cells. , 2011, , .		13
26	Improvement of Read Disturb, Program Disturb and Data Retention by Memory Cell VTH Optimization of Ferroelectric (Fe)-NAND Flash Memories for Highly Reliable and Low Power Enterprise Solid-State Drives (SSDs). IEICE Transactions on Electronics, 2011, E94-C, 539-547.	0.6	3
27	A 1.0V power supply, 9.3GB/s write speed, Single-Cell Self-Boost program scheme for high performance ferroelectric NAND flash SSD. Solid-State Electronics, 2011, 58, 34-41.	1.4	7
28	Recent Progress in Downsizing FeFETs for Fe-NAND Application. Materials Research Society Symposia Proceedings, 2011, 1337, 49.	0.1	1
29	Recent Advances in Ferroelectric-Gate Field-Effect-Transistor Technology. Integrated Ferroelectrics, 2011, 124, 140-146.	0.7	4
30	Large grain growth by annealing of Ag-covered Bi₂Sr₂CaCu₂O_{8 + Î´}thin films and its application in the fabrication of intrinsic Josephson junctions. Superconductor Science and Technology, 2010, 23, 115006.	3.5	7
31	A Ferroelectric NAND Flash Memory for Low-power and Highly Reliable Enterprise SSDs and a Ferroelectric 6T-SRAM for 0.5V Low-power CPU and SoC. Materials Research Society Symposia Proceedings, 2010, 1250, 1.	0.1	0
32	Recent Progress of Ferroelectric-Gate Field-Effect Transistors and Applications to Nonvolatile Logic and FeNAND Flash Memory. Materials, 2010, 3, 4950-4964.	2.9	66
33	A 1.2 V Power Supply, 2.43 Times Power Efficient, Adaptive Charge Pump Circuit with Optimized Threshold Voltage at Each Pump Stage for Ferroelectric-NAND Flash Memories. Japanese Journal of Applied Physics, 2010, 49, 04DD10.	1.5	5
34	A 0.5-V Six-Transistor Static Random Access Memory with Ferroelectric-Gate Field Effect Transistors. Japanese Journal of Applied Physics, 2010, 49, 121501.	1.5	4
35	Fabrication and characterization of sub-0.6-Âµm ferroelectric-gate field-effect transistors. Semiconductor Science and Technology, 2010, 25, 115013.	2.0	20
36	A Negative Word-Line Voltage Negatively-Incremental Erase Pulse Scheme with Î”V_{TH} = 1/6Î”V_{ERASE} for Enterprise Solid-State Drive Application Ferroelectric-NAND Flash Memories. Japanese Journal of Applied Physics, 2010, 49, 04DD08.	1.5	5

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37	Lowered operation voltage in Pt/SBi₂Ta₂O₉/HfO₂/Si ferroelectric-gate field-effect transistors by oxynitriding Si. Semiconductor Science and Technology, 2010, 25, 055005.	2.0	29
38	A 1.0V power supply, 9.5GByte/sec write speed, Single-Cell Self-Boost program scheme for Ferroelectric NAND Flash SSD. , 2010, , .		10
39	Ferroelectric (Fe)-NAND Flash Memory With Batch Write Algorithm and Smart Data Store to the Nonvolatile Page Buffer for Data Center Application High-Speed and Highly Reliable Enterprise Solid-State Drives. IEEE Journal of Solid-State Circuits, 2010, 45, 2156-2164.	5.4	18
40	Memory window widening of Pt/SrBi₂Ta₂O₉/HfO₂/Si ferroelectric-gate field-effect transistors by nitriding Si. Semiconductor Science and Technology, 2009, 24, 105026.	2.0	19
41	Threshold voltage adjustment of ferroelectric-gate field effect transistors by ion implantation. Semiconductor Science and Technology, 2009, 24, 025012.	2.0	25
42	Operational method of a ferroelectric (Fe)-NAND flash memory array. Semiconductor Science and Technology, 2009, 24, 105029.	2.0	32
43	A zero V<inf>TH</inf> memory cell ferroelectric-NAND flash memory with 32% read disturb, 24% program disturb, 10% data retention improvement for enterprise SSD. , 2009, , .		7
44	A 0.5V operation, 32% lower active power, 42% lower leakage current, ferroelectric 6T-SRAM with V<inf>TH</inf> self-adjusting function for 60% larger St atic Noise Margin. , 2009, , .		8
45	Fabrication of thin-film-type Bi2Sr2CaCu2O8+Îîntrinsic Josephson junctions by pulsed-laser-deposition. Superconductor Science and Technology, 2009, 22, 125004.	3.5	10
46	FeCMOS logic inverter circuits with nonvolatile-memory function. IEICE Electronics Express, 2009, 6, 831-836.	0.8	17
47	Threshold-voltage distribution of Pt/SrBi2Ta2O9/Hfâ€“Alâ€“O/Si MFIS FETs. Semiconductor Science and Technology, 2008, 23, 045011.	2.0	20
48	Highly Scalable Fe(Ferroelectric)-NAND Cell with MFIS(Metal-Ferroelectric-Insulator-Semiconductor) Structure for Sub-10nm Tera-Bit Capacity NAND Flash Memories. , 2008, , .		30
49	Basic operation of novel ferroelectric CMOS circuits. Electronics Letters, 2008, 44, 467.	1.0	27
50	Millimeter-wave radiation from a Teflon dielectric probe and its imaging application. Measurement Science and Technology, 2008, 19, 115501.	2.6	13
51	Optimum ambient N[sub 2] pressure during HfAlO pulsed-laser deposition in Ptâˆ•SBTâˆ•HfAlOâˆ•Si field effect transistors. Journal of Vacuum Science & Technology B, 2008, 26, 1585.	1.3	10
52	Effect of Nitrogen Inclusion into Hf-Al-O Layer on Device Properties of Pt/SrBi2Ta2O9/Hf-Al-O/Si Diodes. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2008, 55, 17-20.	0.2	6
53	Low-magnetic-field operations of intrinsic Josephson junctions with a longc-axis periodicity by artificial critical-current modulations. Superconductor Science and Technology, 2007, 20, S79-S86.	3.5	0
54	Large-area pulsed-laser deposition of dielectric and ferroelectric thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 903-907.	2.1	29

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55	Statistical Threshold-Voltage Distribution and Elevated-Temperature Operations of Pt/SrBi<inf>2</inf>Ta<inf>2</inf>O<inf>9</inf>/Hf-Al-O/Si MFIS FETs. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
56	Characterization of Ptâˆ•SrBi2Ta2O9âˆ•Hfâ€“Alâ€“Oâˆ•Si field-effect transistors at elevated temperatures. Applied Physics Letters, 2006, 89, 222910.	3.3	50
57	Leakage current of multiferroic (Bi0.6Tb0.3La0.1)FeO3 thin films grown at various oxygen pressures by pulsed laser deposition and annealing effect. Journal of Applied Physics, 2006, 99, 054104.	2.5	165
58	The fabrication and electrical properties of critical-current-modulated intrinsic Josephson junctions in Bi2Sr2Ca1âˆ’yYyCu2Ox/Bi2Sr2CaCu2Ox stacks. Superconductor Science and Technology, 2006, 19, 459-461.	3.5	1
59	Gate Materials and Fabrication-Processes of Metal-Ferroelectric-Insulator-Semiconductor Memory FETs with Long Data Retention. Advances in Science and Technology, 2006, 45, 2382.	0.2	3
60	Properties of a dielectric probe for scanning near-field millimeter-wave microscopy. Journal of Applied Physics, 2006, 99, 056105.	2.5	9
61	Face-to-face annealing of Bi2Sr2CaCu2Ox thin films for intrinsic Josephson junctions with uniform critical currents. Physica C: Superconductivity and Its Applications, 2005, 426-431, 1474-1478.	1.2	12
62	Self-Aligned-Gate Metal/Ferroelectric/Insulator/Semiconductor Field-Effect Transistors with Long Memory Retention. Japanese Journal of Applied Physics, 2005, 44, L800-L802.	1.5	114
63	Theoretical and numerical study on multistacked Josephson junctions with a parametric modulation of their critical currents. Physical Review B, 2005, 72, .	3.2	3
64	Growth of High-Quality Single-Phase Bi2Sr2CaCu2OxWhiskers by a New Growthâ€“Meltâ€“Regrowth Method. Japanese Journal of Applied Physics, 2004, 43, 3378-3380.	1.5	4
65	Pt/SrBi2Ta2O9/Hf-Al-O/Si Field-Effect-Transistor with Long Retention Using Unsaturated Ferroelectric Polarization Switching. Japanese Journal of Applied Physics, 2004, 43, 7876-7878.	1.5	54
66	Fabrication and electrical properties of ferroelectric-gate FETS with epitaxial gate structures. Electronics and Communications in Japan, 2004, 87, 24-33.	0.2	0
67	Resonant characteristics of twofold Josephson junctions with various critical current ratio. Physica C: Superconductivity and Its Applications, 2004, 412-414, 1468-1472.	1.2	4
68	Characteristics of intrinsic Josephson junctions using a Bi2Sr2CaCu2Ox thin film estimated overall in a chip. Physica C: Superconductivity and Its Applications, 2004, 412-414, 1410-1413.	1.2	5
69	Composition analysis of modified layer in YBCO trilayer interface-engineered Josephson junctions. Physica C: Superconductivity and Its Applications, 2004, 412-414, 1419-1423.	1.2	0
70	Temperature dependence of composition ratio of Bi2Sr2CaCu2O8+Î´ film by PLD method. Physica C: Superconductivity and Its Applications, 2004, 412-414, 1354-1357.	1.2	20
71	Metalâ€“Ferroelectricâ€“Insulatorâ€“Semiconductor Memory FET With Long Retention and High Endurance. IEEE Electron Device Letters, 2004, 25, 369-371.	3.9	200
72	Unified theory for magnetic and electric field coupling in multistacked Josephson junctions. Physical Review B, 2004, 70, .	3.2	33

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73	Memory properties of a ferroelectric gate field-effect transistor with an adjoining metalâ€“ferroelectricâ€“metal assistance cell. Journal of Applied Physics, 2003, 94, 2559-2562.	2.5	14
74	Growth of Single Phase Bi2Sr2CaCu2OxWhiskers Using Optimized Starting Compositions for Glassy Precursors. Japanese Journal of Applied Physics, 2003, 42, 5022-5023.	1.5	4
75	Super-relativistic fluxon in a Josephson multilayer:â€ƒExperiment and simulation. Physical Review B, 2002, 66, .	3.2	30
76	Flux-flow cavity resonance modes in intrinsic Josephson junctions by Bi2Sr2CaCu2Ox thin films. Physica C: Superconductivity and Its Applications, 2002, 367, 404-409.	1.2	9
77	Growth and characterization of potassium tantalate niobate single crystals by the step-cooling technique. Journal of Crystal Growth, 2002, 237-239, 694-699.	1.5	9
78	Description of intrinsic Josephson junctions by the inductive coupling theory. Physica C: Superconductivity and Its Applications, 2001, 362, 1-9.	1.2	3
79	Fabrication and critical currents of thin-film-type Bi2Sr2CaCu2Ox intrinsic Josephson junctions. Physica C: Superconductivity and Its Applications, 2001, 362, 256-260.	1.2	10
80	Fabrication and Electrical Characteristics of a Trench-Type Metal-Ferroelectric-Metal-Insulator-Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2001, 40, 5605-5609.	1.5	1
81	Epitaxial structure SrTiO3ã€ˆ011ã€‰ on Siã€ˆ001ã€‰. Journal of Applied Physics, 2001, 89, 5421-5424.	2.5	21
82	All-perovskite-oxide ferroelectric memory transistor composed of Bi2Sr2CuOx and PbZr0.5Ti0.5O3 films. Journal of Applied Physics, 2001, 89, 8153-8158.	2.5	13
83	Epitaxial structure SrBi2Ta2O9<116> /SrTiO3<011> /Ce0.12Zr0.88O2<001> /Si<001> for ferroelectric-gate FET memory. Integrated Ferroelectrics, 2001, 40, 135-143.	0.7	5
84	Plasma resonance and flux dynamics in layered high-Tc superconductors. Physica C: Superconductivity and Its Applications, 2000, 332, 297-301.	1.2	3
85	Epitaxial Growth of Bi4Ti3O12/CeO2/Ce0.12Zr0.88O2and Bi4Ti3O12/SrTiO3/Ce0.12Zr0.88O2Thin Films on Si and Its Application to Metal-Ferroelectric-Insulator-Semiconductor Diodes. Japanese Journal of Applied Physics, 2000, 39, 5505-5511.	1.5	6
86	Prediction of half harmonic generation in stacked Josephson junctions andBi2Sr2CaCu2Oxsingle crystals. Physical Review B, 2000, 61, 11328-11331.	3.2	4
87	Growth Style of Bi4Ti3O12Thin Films on CeO2/Ce0.12Zr0.88O2Buffered Si Substrates. Japanese Journal of Applied Physics, 1999, 38, 5411-5416.	1.5	10
88	Interaction induced by nonuniform self-fields in stacks of two long Josephson junctions. IEEE Transactions on Applied Superconductivity, 1999, 9, 3953-3956.	1.7	0
89	Memory properties of SrBi2Ta2O9 thin films prepared on SiO2/Si substrates. Applied Physics Letters, 1999, 75, 1613-1615.	3.3	61
90	Plasma resonance in anisotropic layeredhighâ˜Tcsuperconductors. Physical Review B, 1999, 60, 9810-9816.	3.2	14

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91	Particle-free superconducting Bi2Sr2CaCu2Ox ultrathin films prepared by atomic-layer-controlled molecular beam epitaxy technique. Physica C: Superconductivity and Its Applications, 1999, 311, 42-48.	1.2	14
92	Epitaxial Bi4Ti3O12 thin film growth using Bi self-limiting function. Journal of Crystal Growth, 1999, 200, 161-168.	1.5	24
93	Pulsed laser deposition and ferroelectric properties of SrBi2Ta2O9 thin films. Materials Letters, 1999, 38, 406-412.	2.6	12
94	Josephson plasma resonance in superconducting multilayers. Physical Review B, 1998, 58, 2820-2826.	3.2	43
95	Dynamics of multiple-junction stacked flux-flow oscillators: Comparison between theory and experiment. Physical Review B, 1998, 58, 5777-5782.	3.2	23
96	Submillimeter-band high-power generation using multilayered Josephson junctions. Applied Physics Letters, 1998, 73, 686-688.	3.3	57
97	Maximum supercurrent in two Josephson-junction stacks: Theory and experiment. Physical Review B, 1998, 58, 6497-6505.	3.2	9
98	Bunched fluxon states in one-dimensional Josephson-junction arrays. Physical Review B, 1998, 57, 11691-11697.	3.2	38
99	Molecular beam epitaxial growth of BSCCO and Bi-based oxides: self-limiting growth of the Bi element. , 1998, , .		0
100	Self-limiting process for the bismuth content in molecular beam epitaxial growth of Bi2Sr2CuOy thin films. Applied Physics Letters, 1997, 71, 3712-3714.	3.3	36
101	Atomic absorption spectroscopy system for flux monitoring and atomic-layer control of molecular beam epitaxial growth of BiSrCaCuO. Review of Scientific Instruments, 1997, 68, 2850-2855.	1.3	22
102	Nanometer level etching and deposition of Bi-Sr-Ca-Cu-O superconducting thin films. , 1996, , .		4
103	Digital laser etching of Bi-Sr-Ca-Cu-O superconducting thin films. Thin Solid Films, 1996, 281-282, 513-516.	1.8	1
104	Molecular beam epitaxial growth of SrO and CaO with RHEED intensity oscillation. Journal of Low Temperature Physics, 1996, 105, 1337-1342.	1.4	13
105	A Digital Method of Gas Laser Etching for Oxide Superconductors. Japanese Journal of Applied Physics, 1996, 35, L94-L96.	1.5	4
106	Numerical study of fluxon dynamics in a system of twoâ€stacked Josephson junctions. Journal of Applied Physics, 1995, 77, 1171-1177.	2.5	37
107	Dynamic behavior of Josephson-coupled layered structures. Physical Review B, 1994, 50, 3942-3952.	3.2	205
108	Electric-field effects in metal-insulator-superconductor diodes: possibility of singularity in capacitance-voltage relationships. Physica B: Condensed Matter, 1994, 194-196, 2399-2400.	2.7	0

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109	Theory and experiment on electromagnetic-wave-propagation velocities in stacked superconducting tunnel structures. Physical Review B, 1994, 50, 12905-12914.	3.2	154
110	Fluxons in thinâ€film superconductorâ€insulator superlattices. Journal of Applied Physics, 1993, 73, 2411-2418.	2.5	391
111	Theoretical study of electric-field effects in high-Tcoxide superconductors using an ultrathin-metal-insulator superlattice model. Physical Review B, 1993, 47, 9042-9047.	3.2	20
112	Molecular Beam Epitaxy Fabrication of SrTiO3and Bi2Sr2CaCu2O8Heterostructures Using a Novel Reflection High-Energy Electron Diffraction Monitoring Technique. Japanese Journal of Applied Physics, 1992, 31, L949-L952.	1.5	23
113	RHEED Intensity Monitored Growth of Bi-Sr-Ca-Cu-O Superconductors. Japanese Journal of Applied Physics, 1992, 31, L399-L401.	1.5	11
114	Rheed Intensity Monitored Growth of Bi-Sr-Ca-Cu-O Superconductors. Materials Research Society Symposia Proceedings, 1992, 275, 73.	0.1	3
115	Atomic layer by atomic layer growth of Biî—¸Srî—¸Caî—¸Cu oxide superconducting thin films by molecular beam epitaxy. Physica C: Superconductivity and Its Applications, 1991, 185-189, 2013-2014.	1.2	4
116	In-situ growth of Bi-Sr-Ca-Cu oxide superconducting thin films by molecular beam epitaxy with a pure ozone source. Journal of Crystal Growth, 1991, 115, 758-761.	1.5	12
117	Laser Etching of Bi-Sr-Ca-Cu-O Superconducting Thin Films. Japanese Journal of Applied Physics, 1991, 30, L355-L357.	1.5	2
118	In-Situ Growth of Bi-Sr-Ca-Cu-O Thin Films by Molecular Beam Epitaxy. , 1991, , 1085-1088.		1
119	Analytic solutions for bunched two-fluxon states in Josephson transmission lines. Physical Review B, 1987, 36, 812-814.	3.2	6
120	Direct observation of fluxon reflection in a Josephson transmission line. Physical Review B, 1987, 35, 5357-5360.	3.2	17
121	Perturbation analysis of a parametrically changed sine-Gordon equation. Physical Review B, 1987, 36, 217-225.	3.2	25
122	Criteria for fluxon generation in long Josephson junctions by current pulses. Applied Physics Letters, 1987, 50, 1107-1109.	3.3	7
123	Analytical and numerical results for a long Josephson junction with surface losses. IEEE Transactions on Magnetics, 1987, 23, 1114-1117.	2.1	4
124	Bunching of Solitons in Long Josephson Junctions. Japanese Journal of Applied Physics, 1987, 26, 1579.	1.5	7
125	Reflection Properties of Fluxon in a Josephson Transmission Line. Japanese Journal of Applied Physics, 1987, 26, 1573.	1.5	0
126	Measurements of the high frequency loss near the plasma resonance in Josephson tunnel junctions. IEEE Transactions on Magnetics, 1987, 23, 1118-1121.	2.1	0

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127	Analytic solution for fluxons in a long Josephson junction with surface losses. Physical Review B, 1986, 34, 3506-3509.	3.2	17
128	Real time fluxon dynamics in josephson transmission line. IEEE Transactions on Magnetics, 1985, 21, 737-740.	2.1	31
129	Fluxon Transfer Device. Japanese Journal of Applied Physics, 1985, 24, L771-L773.	1.5	13
130	Fluxon Divider. Japanese Journal of Applied Physics, 1985, 24, L749-L751.	1.5	3
131	Fluxon Feedback Oscillator. Japanese Journal of Applied Physics, 1984, 23, L610-L612.	1.5	19
132	Fluxon Devices. , 1984, , .		0
133	A Direct Coupled Josephson Sampler. Japanese Journal of Applied Physics, 1983, 22, L435-L437.	1.5	23
134	Fluxon Observation Using a Josephson Sampler. Japanese Journal of Applied Physics, 1983, 22, L479-L481.	1.5	20
135	Analytical Solutions of Traveling Fluxon Waves on a Josephson Transmission Line with Shunt Conductance and Uniform Bias Current. Japanese Journal of Applied Physics, 1983, 22, 1374-1381.	1.5	17
136	Travelling Waves on a Josephson Transmission Line. Japanese Journal of Applied Physics, 1983, 22, 161-170.	1.5	8
137	Fluxon Waves on a Josephson Transmission Line. Japanese Journal of Applied Physics, 1982, 21, L7-L9.	1.5	5
138	Quasiparticle-Injected Superconducting Weak Link Device. Japanese Journal of Applied Physics, 1982, 21, 331.	1.5	3
139	Static characteristic of a new quasiparticle injected superconducting weak link device. Electronics Letters, 1981, 17, 501.	1.0	5
140	Quasiparticle-Injected Superconducting Weak Link Device. , 1981, , .		2
141	Nb/GaAs super-Schottky diode. IEEE Electron Device Letters, 1980, 1, 236-238.	3.9	6
142	Energy band of ternary alloy semiconductorsâ€”Calculation by a coherentâ€potential approximation based on the method of linear combination of bond orbitals. Journal of Applied Physics, 1979, 50, 4143-4155.	2.5	15
143	Optical Properties of Vacuum-Deposited CdCr2Se4Thin Film. Japanese Journal of Applied Physics, 1976, 15, 2023-2024.	1.5	10
144	Long-retention ferroelectric-gate FET with a (HfO/sub 2/)/sub x/(Al/sub 2/O/sub 3/)/sub 1-x buffer-insulating layer for 1T FeRAM. , 0, , .		8